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Test results of TaichuPix chips

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TaichuPix chips overview





TaichuPix-1 Chip size: 5 mm \times 5 mm Pixel size: 25 μ m \times 25 μ m



TaichuPix-2 Chip size: 5 mm \times 5 mm Pixel size: 25 μ m \times 25/24 μ m

• Two MPW chips were fabricated and verified

- > TaichuPix-1: 2019.06~2019.11
- > TaichuPix-2: 2020.02~2020.06

Chip size 5 mm×5 mm with standalone features

- > Pixel size of 25 μ m×25 μ m (one sector with 25 μ m×24 μ m pixels in TaichuPix-2)
- A full functional pixel array (small scale)
 - A 64×192 Pixel array (including 6 pixel variations)
- Periphery logics
 - Fully integrated logics for the data-driven readout
 - Fully digital control of the chip configuration
- > Auxiliary blocks for standalone operation
 - High speed data interface up to 4Gbps
 - On-chip bias generation
 - Power management with LDOs
 - IO placement in the final ladder manner
 - Multiple chip interconnection features included



Electrical test

 Electrical performance verified by injecting an external voltage step (charge) into pixel front-end





Threshold distribution measured on S1-S4

 Based on the same bias condition for pixel analog, S-curves measured for S1-S4 (with different pixel analog designs)



Noise distribution measured on S1-S4



The measured threshold and noise difference between different sectors agree with design qualitatively.



Comparison of ENC and Charge Threshold

- Converting the noise/threshold voltage to electrons by 0.88 mV/e⁻
 - Assuming the charge injection capacitance in each pixel is 0.18 fF, which is extracted from layout

	eliminan	Threshold Mean	Threshold RMS	ENC	ENC Std. dev
9	S1	282.1 e ⁻	52.7 e⁻	31.0 e⁻	5.1 e⁻
	S2	310.1 e⁻	57.6 e⁻	28.4 e⁻	6.4 e⁻
	S3	406.8 e⁻	61.7 e⁻	25.8 e⁻	6.3 e⁻
	S4	435.3 e⁻	59.8 e⁻	28.0 e ⁻	7.3 e⁻

ENC and charge threshold in this table only for comparison of different sectors, but the absolute value can not used for the sensor assessment

 Factor of charge to voltage (0.88 mV/e- in simulation) need to be calibrated

Threshold distribution measured on S1

- S-curves measured on different bias conditions of front-end for S1
- The effect of bias condition on threshold coincides with design



Noise distribution measured on S1





TaichuPix-1 response to ⁹⁰Sr





- Analog signals of a pixel were captured with oscilloscope.
- Larger signal having smaller peak time and pulse duration, agrees with simulation
- TaichuPix-2 will be tested with ⁹⁰Sr soon

Preliminary verification with radioactive



- Analog output waveform agreed with the simulation when tested by X-rays
- Signal amplitude, signal width, edge speed...all are almost agreed
- Note: for the small signal, the S/N ratio was also good, inferred that the noise performance was also normal (good)



Pixel dimension test (Preliminary)





- Laser was moved every 200 µm in X/Y direction, the center of the light spot was used for position
- Linear fit was done with interpolation if the center was found at 2 pixels

Pixel dimension test (Preliminary)





- -7.762±0.05 & 1/(0.162±0.007) were found as the fitted pixels per 200um, while estimated pixels were 8
- The reason was the test board surface was not fixed vertically to the platform, due to the heavy extension cable of the KC705



Summary and plan



- Major functionality proved stable by the full readout system
 - > Minor bugs will be fixed in the next version
- Test with ⁹⁰Sr source, TID test, laser test will be done
- Preparation for the next version chip
 - > A engineering run is proposed

Backup



Sector	Pixel front-end	Pixel digital	Pixel size
Sector 1	Same as S1 of TC1, reference design	FEI3-like	25 µm × 25 µm
Sector 2	M6 with guard-ring, PMOS in independent nwell	FEI3-like	25 µm × 25 µm
Sector 3	M6 in enclosed layout, PMOS in independent nwell	FEI3-like	25 µm × 24 µm
Sector 4	Increasing M3, M4, M9. M6 in enclosed layout, PMOS in independent nwell	FEI3-like	25 µm × 25 µm
Sector 5	Same FE as S1, with smaller sensor	ALPIDE-like	25 µm × 25 µm
Sector 6	Same FE as S1	AI PIDE-like	25 µm x 25 µm





6 Jan. 2021, CEPC Physics and Detector Plenary meeting

X-ray imaging







"single frame" X-ray imaging with 10s exposure @ 8kV X-ray tube

- "DAQ" system established for the test system, with continuous data acquisition
- Triggerless readout @160Mbps LVDS were applied at the current stage
- The full signal chain (pixel analog-digital-periphery-data interface) was proved by both X-ray and laser imaging
 - Full array/sector was sensitive
 - Single frame imaging showing no crosstalk detected between clusters (good S/N ratio)
- X-ray imaging with 5 min exposure showed clearly the different sectors of the pixel array (2 sectors were masked)